

1. General description

Planar passivated thyristor module in industrial standard 34mm package for use in applications requiring high blocking voltage capability, high inrush current capability and high thermal cycling performance.

2. Features and benefits

- High blocking voltage capability
- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- Product is RoHS compliant
- Industry standard outline
- Copper base plate
- Cathode Kelvin contacts provided

3. Applications

- Softstart AC motor control
- DC Motor control
- AC Motor control
- Power converter
- Temperature control
- Lighting control

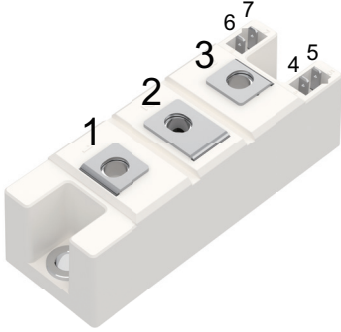
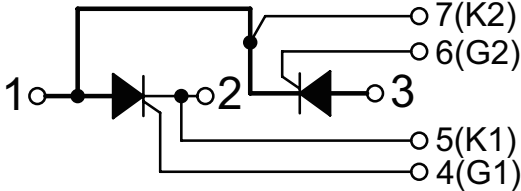
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute maximum rating							
V _{DRM}	repetitive peak forward voltage			1600			V
V _{RRM}	repetitive peak reverse voltage			1600			V
I _{T(RMS)}	RMS on-state current	half sine wave; T _c = 87 °C		314			A
I _{TSM}	non-repetitive peak on-state current	half sine wave; T _{j(init)} = 25 °C; t _p = 10 ms		5600			A
		half sine wave; T _{j(init)} = 135 °C; t _p = 10 ms		5100			A
		half sine wave; T _{j(init)} = 25 °C; t _p = 8.3 ms		6160			A
		half sine wave; T _{j(init)} = 135 °C; t _p = 8.3 ms		5610			A
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.2 A; T _j = 25 °C		-	-	150	mA
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.2 A; T _j = 25 °C		-	-	2	V
V _T	on-state voltage	I _T = 200 A; T _j = 25 °C		-	-	1.3	V

5. Pinning information

Table 2. Pinning information

Simplified outline	Graphic symbol
	

6. Ordering information

Table 3. Ordering information

Type number	Orderable part number	Packing method	Small packing quantity
WTMH200S16	WTMH200S16T	Tray	16

7. Marking

Table 4. Marking codes

Type number	Marking codes
WTMH200S16	WTMH200S16

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{DSM}	Non-repetitive peak forward voltage			1700	V
V_{RSM}	Non-repetitive peak reverse voltage			1700	V
V_{DRM}	repetitive peak forward voltage			1600	V
V_{RRM}	repetitive peak reverse voltage			1600	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_c = 87\text{ }^{\circ}\text{C}$		200	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_c = 87\text{ }^{\circ}\text{C}$		314	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{J(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$		5600	A
		half sine wave; $T_{J(\text{init})} = 135\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$		5100	A
		half sine wave; $T_{J(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 8.3\text{ ms}$		6160	A
		half sine wave; $T_{J(\text{init})} = 135\text{ }^{\circ}\text{C}$; $t_p = 8.3\text{ ms}$		5610	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse		156.8	kA^2s
dI_T/dt	rate of rise of on-state current	$I_G = 300\text{ mA}$		200	$\text{A}/\mu\text{s}$
P_{GM}	peak gate power			120	W
$P_{G(AV)}$	average gate power	over any 20 ms period		20	W
T_{vj}	virtual junction temperature			-40 to 135	$^{\circ}\text{C}$
T_{op}	operation temperature			-40 to 135	$^{\circ}\text{C}$
T_{stg}	storage temperature			-40 to 150	$^{\circ}\text{C}$

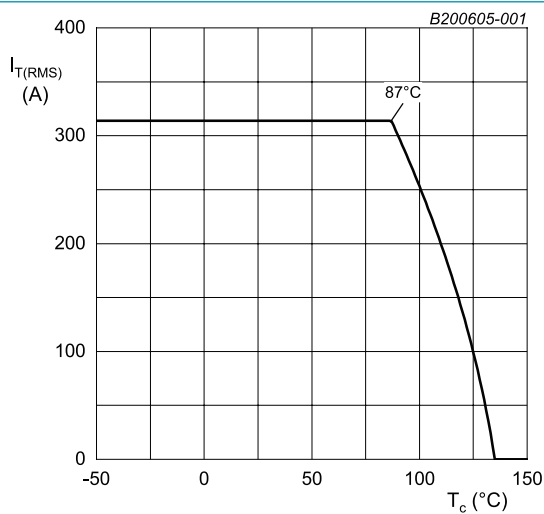
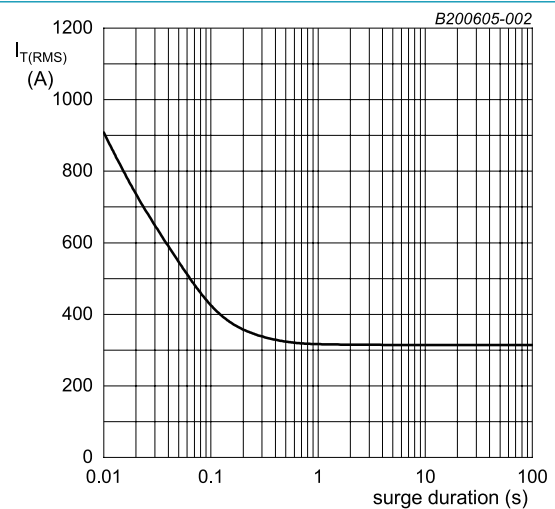


Fig. 1. RMS on-state current as a function of case temperature; maximum values



$f = 50\text{ Hz}$; $T_c = 87\text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

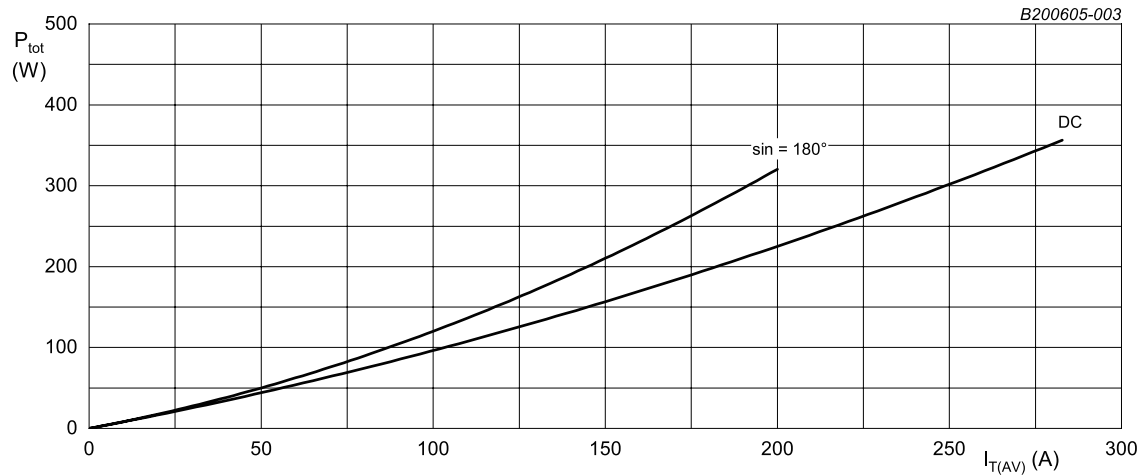
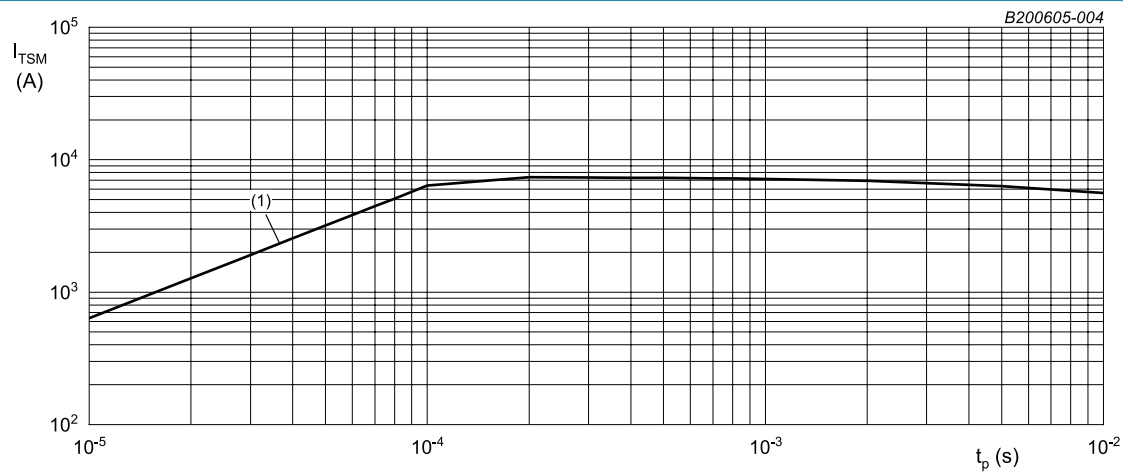


Fig. 3. Total power dissipation as a function of average on-state current; maximum values; per thyristor



$t_p \leq 10\text{ ms}$
(1) di_T/dt limit

Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	per thyristor		-	-	0.15	K/W
		per module		-	-	0.075	K/W
$R_{th(c-h)}$	thermal resistance from case to heatsink	per thyristor		-	-	0.1	K/W
		per module		-	-	0.05	K/W

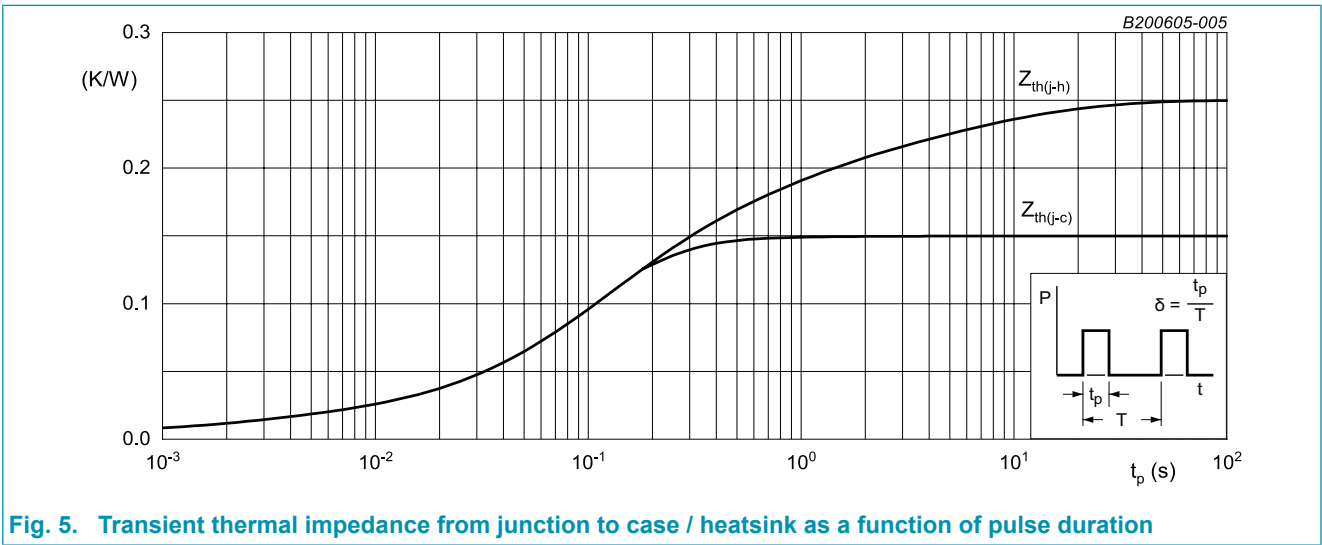


Fig. 5. Transient thermal impedance from junction to case / heatsink as a function of pulse duration

10. Package characteristics

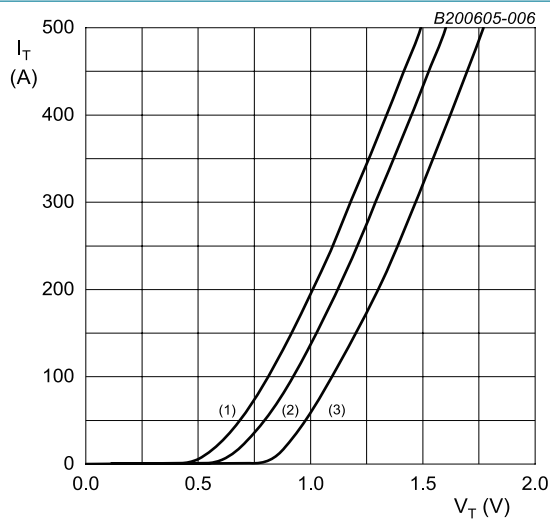
Table 7. Isolation characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{isol}	isolation voltage	50/60 Hz; RMS; $I_{ISOL} \leq 1$ mA; $t = 1$ second; AC		-	-	3600	V
		50/60 Hz; RMS; $I_{ISOL} \leq 1$ mA; $t = 1$ minute; AC		-	-	3000	V

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.2 A; T _j = 25 °C		-	-	150	mA
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.2 A; T _j = 25 °C		-	-	2	V
		V _D = ⅔ V _{DRM} ; I _T = 0.2 A; T _j = 135 °C		0.25	0.48	-	V
I _{GD}	gate non-trigger current	T _j = 135 °C		-	-	10	mA
V _{GD}	gate non-trigger voltage	T _j = 135 °C		-	-	0.2	V
I _L	latching current	V _D = 12 V; I _T = 0.2 A; T _j = 25 °C		-	-	300	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C		-	-	200	mA
V _T	on-state voltage	I _T = 200 A; T _j = 25 °C		-	-	1.3	V
V _{TO}	threshold voltage	T _j = 135 °C		-	-	0.8	V
r _T	slope resistance	T _j = 135 °C		-	-	1.6	mΩ
I _D	off-state current	V _D = 1600 V; T _j = 25 °C		-	-	100	μA
		V _D = 1600 V; T _j = 135 °C		-	-	10	mA
I _R	reverse current	V _R = 1600 V; T _j = 25 °C		-	-	100	μA
		V _R = 1600 V; T _j = 135 °C		-	-	10	mA
Dynamic characteristics							
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 1072 V; T _j = 135 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit		1500	-	-	V/μs
t _{gt}	gate-controlled turn-on time	V _D = 67% of V _{DRM}		-	-	2	μs
t _q	commutated turn-off time	V _R = 100 V; t _p = 50 μs; dV _D /dt = 5 V/μs; dl/dt = 30 A/μs; T _j = 135 °C		-	150	-	μs



- (1) $T_j = 135^\circ\text{C}$; typical values
- (2) $T_j = 135^\circ\text{C}$; maximum values
- (3) $T_j = 25^\circ\text{C}$; maximum values

Fig. 6. On-state current as a function of on-state voltage

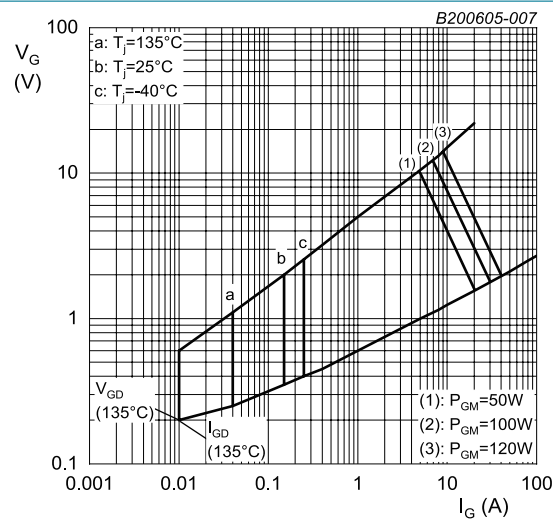
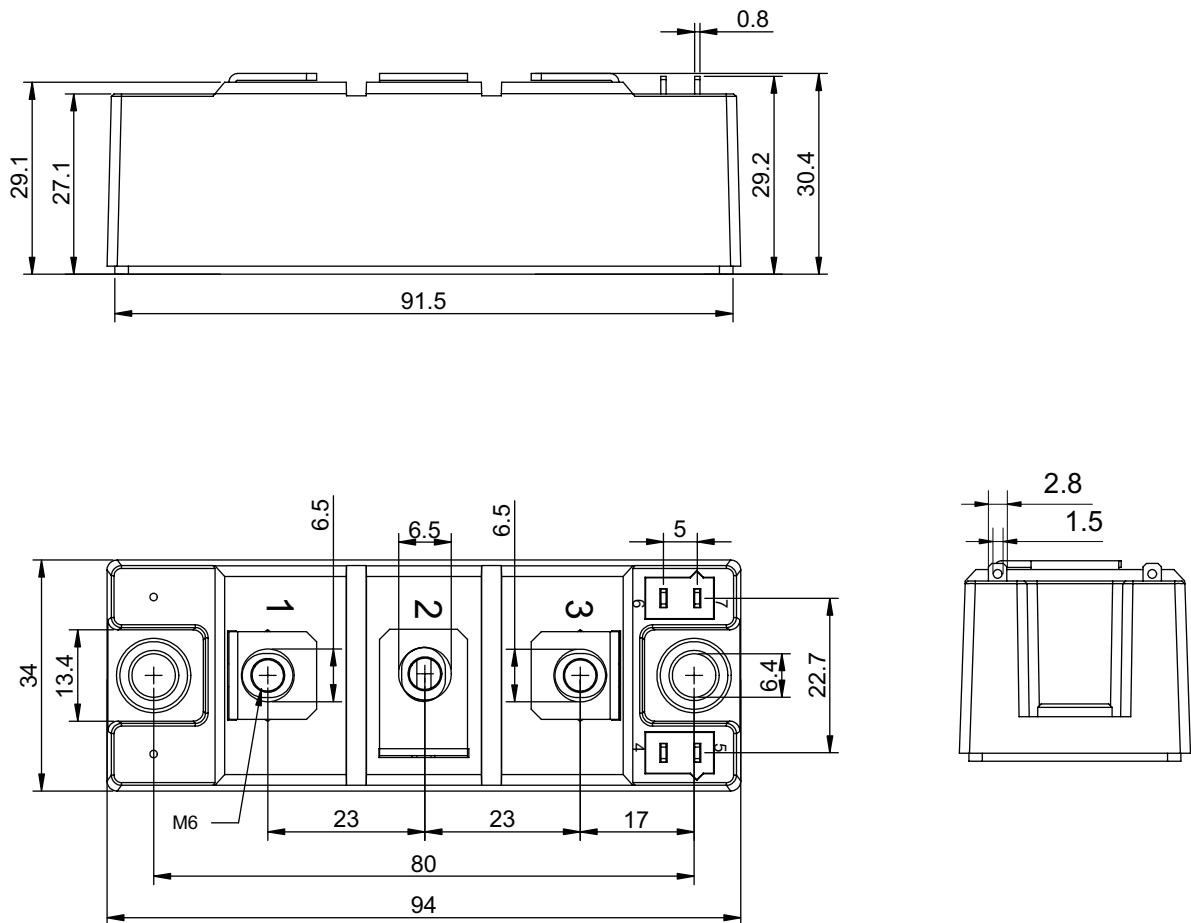


Fig. 7. Gate voltage as a function of gate current

12. Package outline

Dimensions in mm



General tolerance $\pm 0.5\text{mm}$
Signal pins 4-7 are optional, defined by graphic symbol definition.

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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